

VSKT105..., VSKH105..., VSKL105..., VSKN105... Series

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ADD-A-PAK Generation VII Power Modules Thyristor/Diode and Thyristor/Thyristor, 105 A



ADD-A-PAK

PRODUCT SUMMARY					
I _{T(AV)} or I _{F(AV)}	105 A				
Туре	Modules - Thyristor, Standard				

MECHANICAL DESCRIPTION

The ADD-A-PAK Generation VII, new generation of ADD-A-PAK module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

FEATURES

- High voltage
- Industrial standard package



- · Low thermal resistance
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- High surge capability
- · Easy mounting on heatsink

ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	OL CHARACTERISTICS VALUES		UNITS				
I _{T(AV)} or I _{F(AV)}	85 °C	105					
I _{O(RMS)}	As AC switch	235	^				
I _{TSM,}	50 Hz	2000	A				
I _{FSM}	60 Hz	2094					
l ² t	50 Hz	20	kA ² s				
1-1	60 Hz	18.26	KA-S				
$I^2\sqrt{t}$		200	kA²√s				
V _{RRM}	Range	400 to 1600	V				
T _{Stg}		-40 to 130	°C				
T _J		-40 to 130					



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ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM,} I _{DRM} AT 130 °C mA			
	04	400	500	400				
	06	600	700	600	7			
	08	800	900	800				
VSK.105	10	1000	1100	1000	20			
	12	1200	1300	1200				
	14	1400	1500	1400				
	16	1600	1700	1600				

ON-STATE CONDUCTION	OVACO:		TEGT COLUM	TIONS	VAL ::=0	LINUTO
PARAMETER	SYMBOL		TEST COND	HUNS	VALUES	UNITS
Maximum average on-state current (thyristors)	I _{T(AV)}	Į.	180° conduction, half sine wave,		105	
Maximum average forward current (diodes)	I _{F(AV)}	T _C = 85 °C				
Maximum continuous RMS on-state current, as AC switch	I _{O(RMS)}		or ~	(RMS)	235	Α
		t = 10 ms	No voltage		2000	
Maximum peak, one-cycle non-repetitive	I _{TSM}	t = 8.3 ms	reapplied	Sinusoidal	2094	
on-state or forward current	or I _{FSM}	t = 10 ms	100 % V _{RRM}	half wave, initial $T_J = T_J$ maximum	1682	
	·F3W	t = 8.3 ms	reapplied		1760	
		t = 10 ms	No voltage	Initial $T_J = T_J$ maximum	20	kA ² s
Maximum I ² t for fusing	12.	t = 8.3 ms	reapplied		18.26	
	l ² t	t = 10 ms	100 % V _{RBM}		14.14	
		t = 8.3 ms	reapplied		12.91	
Maximum I²√t for fusing	I ² √t ⁽¹⁾		t = 0.1 ms to 10 ms, no voltage reapplied $T_J = T_J$ maximum			kA²√s
Marian and a sulface field affects	V (2)	Low level (3)			0.98	
Maximum value or threshold voltage	V _{T(TO)} (2)	High level (4)	$T_J = T_J \text{ maxin}$	num	1.12	V
Maximum value of on-state	(2)	Low level (3)	- - ·		2.7	
slope resistance	r _t ⁽²⁾	High level (4)	$T_J = T_J$ maximum		2.34	mΩ
	V_{TM}	$I_{TM} = \pi \times I_{T(AV)}$			1.8	.,
Maximum peak on-state or forward voltage	V _{FM}	$I_{FM} = \pi \times I_{F(AV)}$	1 i = 25 °C			V
Maximum non-repetitive rate of rise of	dl/dt	T _J = 25 °C, from 0.67 V _{DRM} ,		150	A/µs	
turned on current	ui/ut	$I_{TM} = \pi \times I_{T(AV)}$, $I_g = 500$ mA, $t_r < 0.5$ μ s, $t_p > 6$ μ s		130	Ανμο	
Maximum holding current	l _Η	T_J = 25 °C, anode supply = 6 V, resistive load, gate open circuit			250	mA
Maximum latching current	ΙL	$T_J = 25 ^{\circ}\text{C}$, and	T _J = 25 °C, anode supply = 6 V, resistive load			

Notes

⁽¹⁾ I^2t for time $t_x = I^2\sqrt{t} \times \sqrt{t_x}$

⁽²⁾ Average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$

 $^{^{(3)}~16.7~\%~}x~\pi~x~I_{AV} < I < \pi~x~I_{AV}$

⁽⁴⁾ $I > \pi \times I_{AV}$



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TRIGGERING					
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}			12	W
Maximum average gate power	P _{G(AV)}			3	VV
Maximum peak gate current	I _{GM}			3	А
Maximum peak negative gate voltage	- V _{GM}			10	
		T _J = -40 °C	Anode supply = 6 V resistive load	4.0	V
Maximum gate voltage required to trigger	V _{GT}	T _J = 25 °C		2.5	
		T _J = 125 °C		1.7	
		T _J = -40 °C	Anode supply = 6 V	270	
Maximum gate current required to trigger	I _{GT}	T _J = 25 °C		150	mA
		T _J = 125 °C	Tesistive load	80	
Maximum gate voltage that will not trigger	V_{GD}	T _J = 125 °C, rated V _{DRM} applied		0.25	V
Maximum gate current that will not trigger	I _{GD}	T _J = 125 °C, rated V _{DRM} applied		6	mA

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM}	I _{RRM,} I _{DRM}	T _J = 130 °C, gate open circuit	20	mA				
Maximum RMS insulation voltage	V _{INS}	50 Hz	3000 (1 min) 3600 (1 s)	V				
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = 130$ °C, linear to 0.67 V_{DRM}	1000	V/µs				

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Junction operating temperature	Junction operating temperature range			- 40 to 130	°C		
Storage temperature range		T _{Stg}		- 40 10 130)		
Maximum internal thermal resistance, junction to case per leg		R _{thJC}	DC operation	0.22	°C/W		
Typical thermal resistance, case to heatsink per module		R _{thCS}	Mounting surface flat, smooth and greased	0.1	C/VV		
	to heatsink		A mounting compound is recommended and the torque should be rechecked after a period	4			
Mounting torque ± 10 % busbar			of 3 hours to allow for the spread of the compound.	3	Nm		
Approximate weight				75	g		
				2.7	OZ.		
Case style			JEDEC®	AAP GEN VI	(TO-240AA)		

△R CONDUCTION PER JUNCTION											
DEVICES		SINE HALF WAVE CONDUCTION RECTANGULAR WAVE CONDUCTION						UNITS			
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.105	0.04	0.048	0.063	0.085	0.125	0.033	0.052	0.067	0.088	0.127	°C/W

Note

Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC





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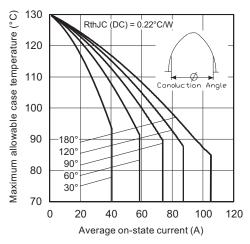


Fig. 1 - Current Ratings Characteristics

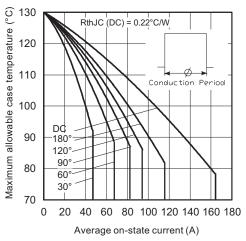


Fig. 2 - Current Ratings Characteristics

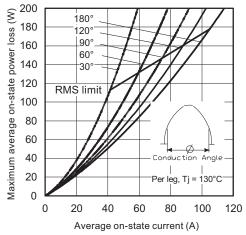


Fig. 3 - On-State Power Loss Characteristics

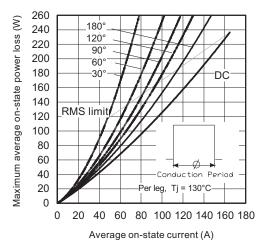
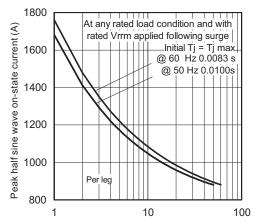


Fig. 4 - On-State Power Loss Characteristics



Number of equal amplitude half cycle current pulses (N)

Fig. 5 - Maximum Non-Repetitive Surge Current

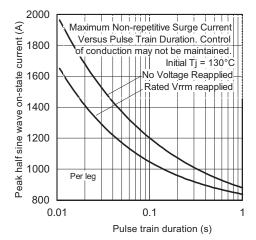


Fig. 6 - Maximum Non-Repetitive Surge Current

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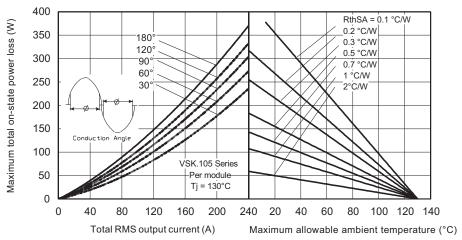


Fig. 7 - On-State Power Loss Characteristics

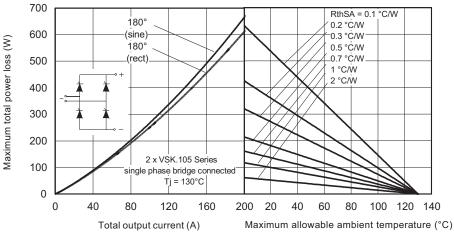


Fig. 8 - On-State Power Loss Characteristics

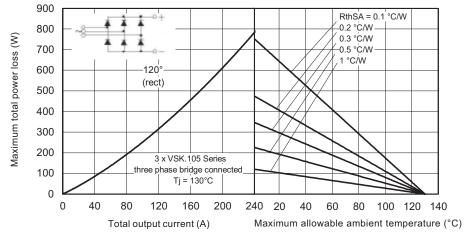


Fig. 9 - On-State Power Loss Characteristics

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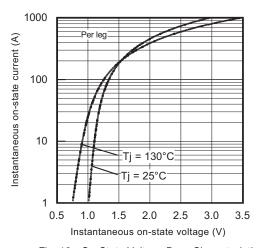


Fig. 10 - On-State Voltage Drop Characteristics

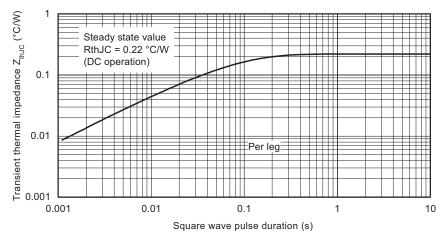


Fig. 11 - Thermal Impedance Z_{thJC} Characteristics

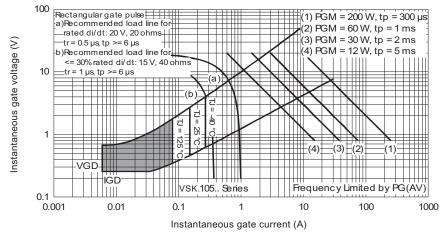


Fig. 12 - Gate Characteristics

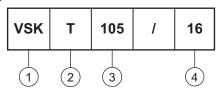
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ORDERING INFORMATION TABLE

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Device code



1 - Module type

2 - Circuit configuration (see end of datasheet)

3 - Current code (105 A)

Voltage code (see Voltage Ratings table)

Note

• To order the optional hardware go to www.vishay.com/doc?95172

CIRCUIT CONFIGURATION							
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING					
Two SCRs doubler circuit	Т	VSKT (1) (1) (2) (2) (3) (4) (5) (7) (6)					
SCR/diode doubler circuit, positive control	Н	VSKH 1 1 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0					
SCR/diode doubler circuit, negative control	Ļ	VSKL 1					
SCR/diode common anodes	N	VSKN (1) (1) (1) (2) (2) (3) (3) (4) (5) (4) (5)					

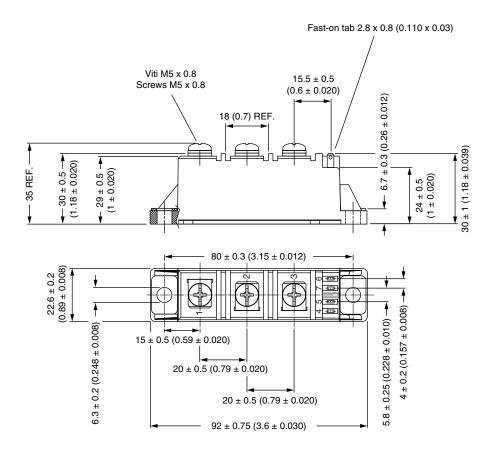
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95368				



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ADD-A-PAK Generation VII - Thyristor

DIMENSIONS in millimeters (inches)





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